





### 60V N-CHANNEL ENHANCEMENT MODE VERTICAL DMOSFET IN SOT23

#### **Features**

- $BV_{DSS} > 60V$
- $R_{DS(on)} \le 2.5\Omega$  @  $V_{GS} = 10V$
- Maximum continuous drain current I<sub>D</sub> = 200mA
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

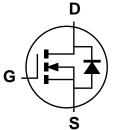
#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method
- Weight: 0.008 grams (approximate)

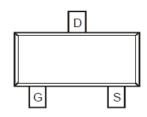








Device symbol



Pin-Out Top View

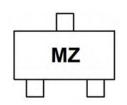
## **Ordering Information** (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVN4106FTA	MZ	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



MZ = Product Type Marking Code



**ZVN4106F** 

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	200	mA
Pulsed Drain Current (Note 5)	I <sub>DM</sub>	3	A

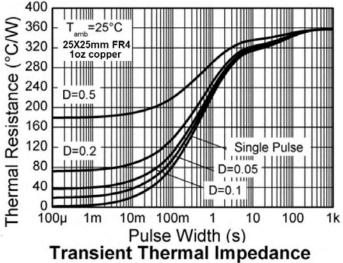
## **Thermal Characteristics**

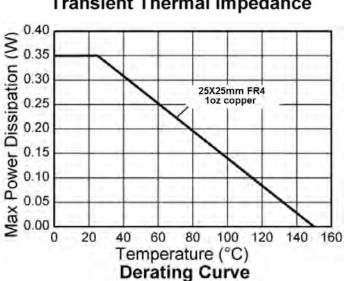
Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	$P_{D}$	350	mW
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	°C	

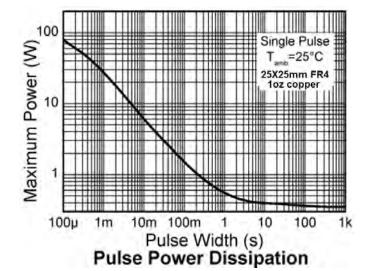
Notes: 5. Device

- 5. Device mounted on minimum recommended pad layout test board, 10 s pulse duty cycle = 1%.
- 6. For a device mounted on 25mm X 25mm X 1.6mm FR-4 PCV with high coverage of single sided 1oz copper, in still air condition.

### Thermal Characteristics









**ZVN4106F** 

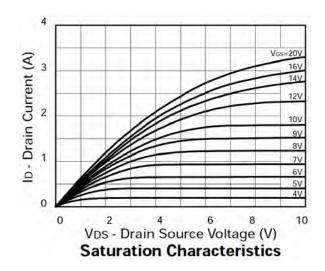
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

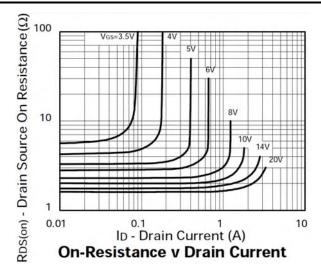
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V$ , $I_D = 10mA$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	l	_	10 50	μΑ	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, V_{GS} = 0V, T_A = +125^{\circ}C$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
On-State Drain Current	I <sub>D(on)</sub>	1	_	-	Α	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V	
ON CHARACTERISTICS (Note 7)	-		ā.				
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.3	_	3	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Static Drain-Source On-Resistance	R <sub>DS (on)</sub>		_	2.5 5	Ω	$V_{GS} = 10V, I_D = 500mA$ $V_{GS} = 5V, I_D = 200mA$	
Forward Transconductance		150	_	-	mS	V <sub>DS</sub> = 25V, I <sub>D</sub> = 250mA	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	_	35	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	_	25	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	8	pF		
Turn-On Delay Time	t <sub>D(on)</sub>	_	_	5	ns	V <sub>DS</sub> = 25V, I <sub>D</sub> = 150mA	
Turn-On Rise Time	t <sub>r</sub>		_	7	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	_	6	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	_	8	ns		

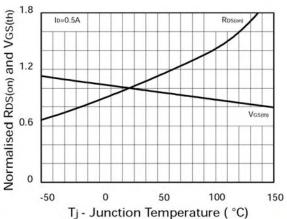
Notes: 7. Short duration pulse test used to minimize self-heating effect.

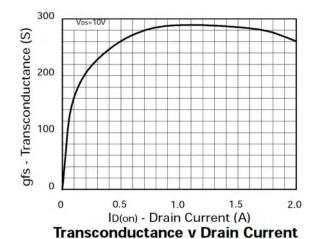


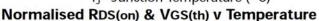
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

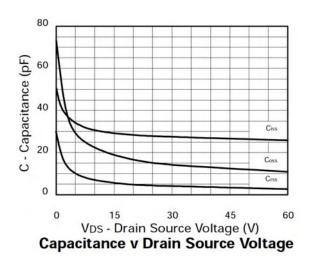


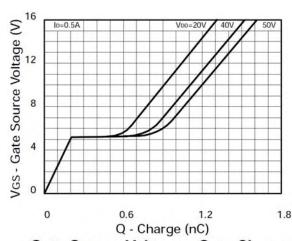








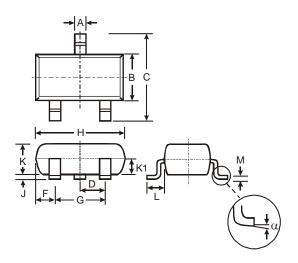




Gate Source Voltage v Gate Charge

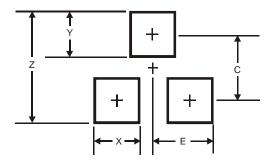


# **Package Outline Dimensions**



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	1	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



**ZVN4106F** 

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